

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

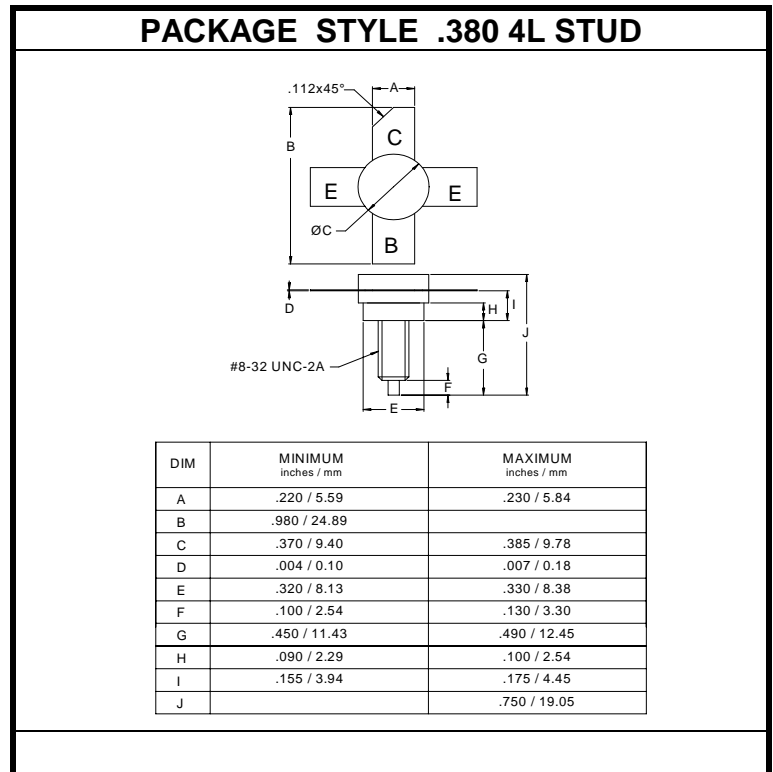
The **ASI BAM80** is Designed for VHF AM power amplifier Applications in the range of 100 to 150 MHz.

FEATURES:

- Common Emitter
- $P_G = 6.0$ dB at 20 W/150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	8.5 A
V_{CES}	60 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	85 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	2.0 °C/W



CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CES}	$I_C = 20$ mA	60			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			2.0	mA
I_{CES}	$V_{CE} = 30$ V $T_C = 125$ °C			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	5.0		---	---
C_{cb}	$V_{CB} = 28$ V $f = 1.0$ MHz			75	pF
P_G η_c V_{SWR}	$V_{CE} = 13.5$ V $P_{OUT} = 20$ W $f = 150$ MHz	6.0 30:1	65		dB % ---

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